Package: SOT-363

Product Description

The SGA3263Z is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high F_T and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

Features

- Broadband Operation: DC to 5500 MHz
- Cascadable 50Ω
- Operates from Single Supply
- Low Thermal Resistance Package

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Optimum Technology Matching® Applied

☐	GaAs HBT
☐	GaAs MESFET
☐	InGaP HBT
☐	SiGe BiCMOS
☐	Si BiCMOS
✓	SiGe HBT
☐	GaAs pHEMT
☐	Si CMOS
☐	Si BJT
☐	GaN HEMT
☐	RF MEMS

Gain & Return Loss vs. Frequency
V_D = 2.6 V, I_D = 35 mA (Typ.)

T_L = +25ºC
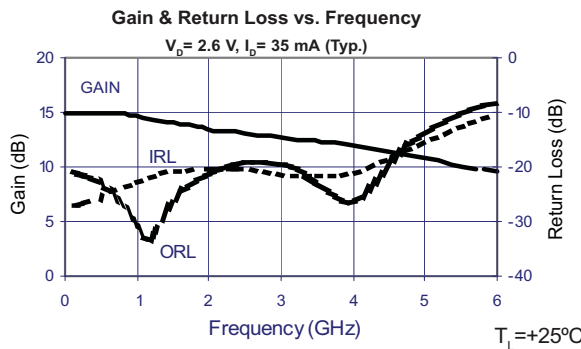
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Small Signal Gain	13.5	15.0	16.5	dB	850 MHz
		13.6		dB	1950 MHz
		13.3		dB	2400 MHz
Output Power at 1dB Compression		11.6		dBm	850 MHz
		10.9		dBm	1950 MHz
Output Third Intercept Point		26.2		dBm	850 MHz
		24.1		dBm	1950 MHz
Bandwidth Determined by Return Loss		5500		MHz	>10 dB
Input Return Loss		20.3		dB	1950 MHz
Output Return Loss		21.5		dB	1950 MHz
Noise Figure		3.8		dB	1950 MHz
Device Operating Voltage	2.3	2.6	2.9	V	
Device Operating Current	31	35	39	mA	
Thermal Resistance (Junction - Lead)		255		°C/W	

Test Conditions: V_S=5V, I_D=35 mA Typ., OIP_3 Tone Spacing=1 MHz, P_{OUT} per tone=-5 dBm, R_{BIAS}=68Ω, T_L=25°C, Z_S=Z_L=50Ω

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1 of 7

SGA3263Z

Absolute Maximum Ratings

Parameter	Rating	Unit
Max Device Current (I_D)	70	mA
Max Device Voltage (V_D)	4	V
Max RF Input Power	+18	dBm
Max Junction Temp (T_J)	+150	°C
Operating Temp Range (T_L)	-40 to +85	°C
Max Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$$I_D V_D < (T_J - T_L) / R_{TH, j\text{-}l}$$

⚠ **Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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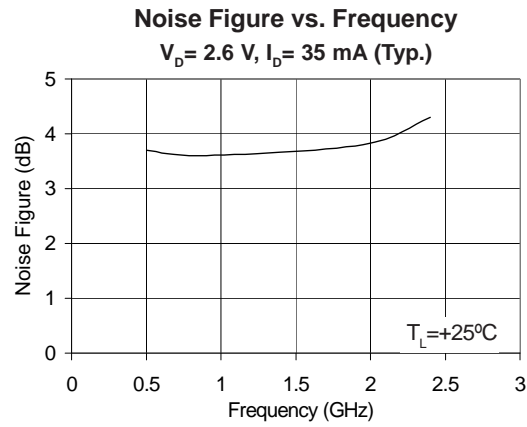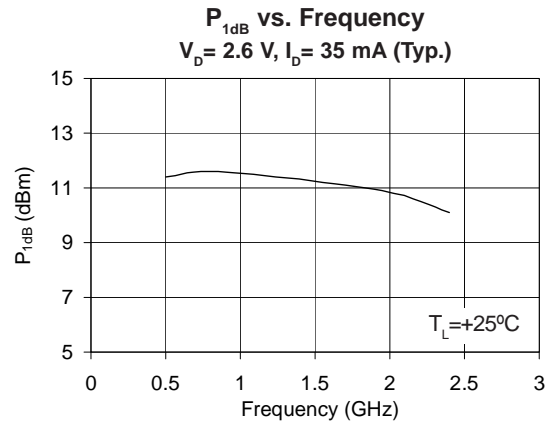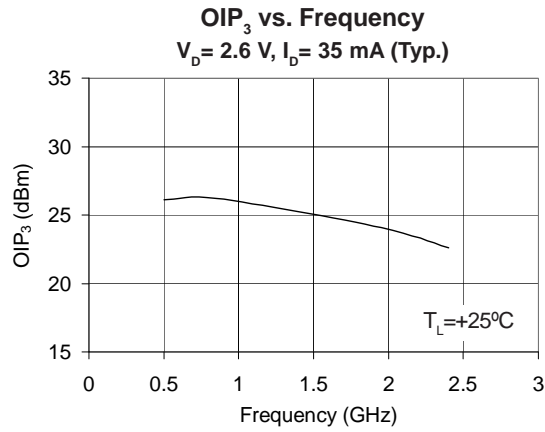
RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.
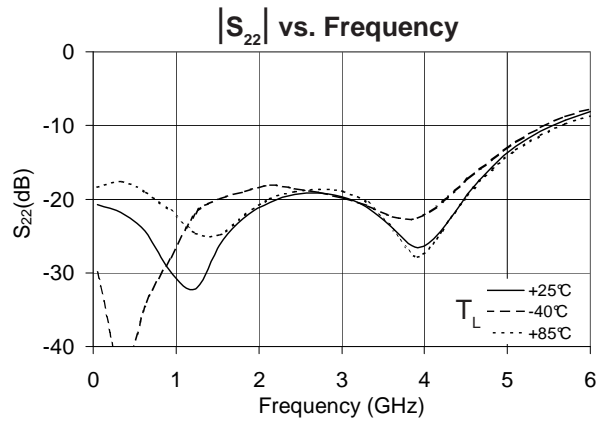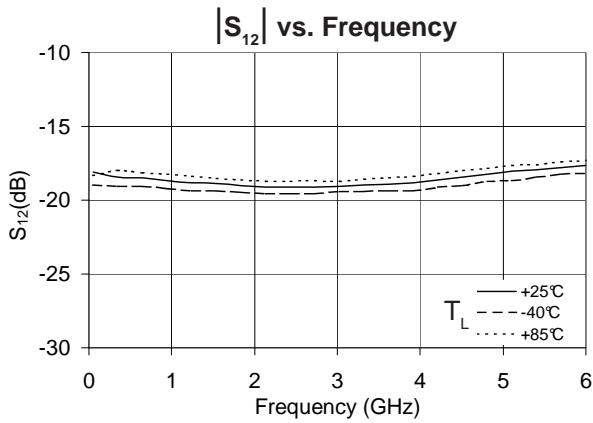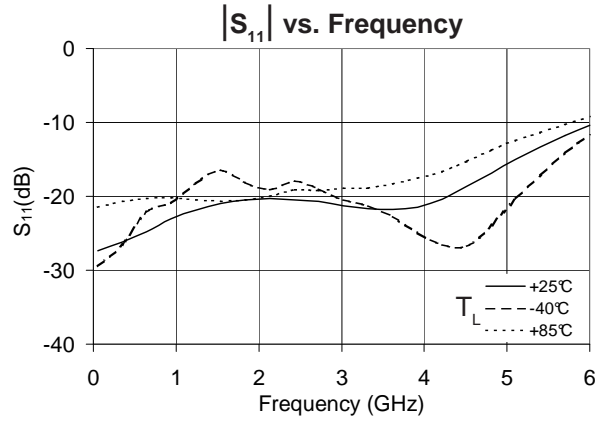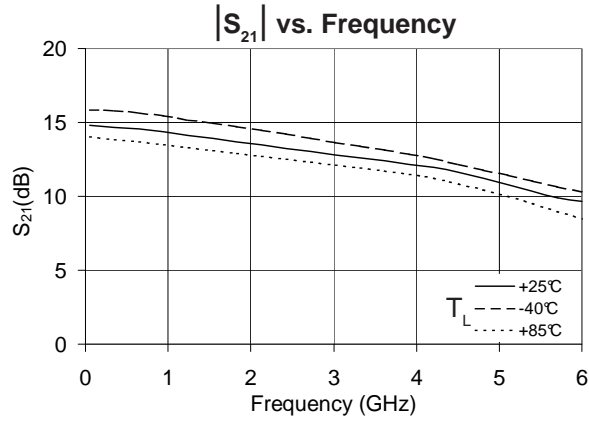
Typical Performance at Key Operating Frequencies

Parameter	Unit	100 MHz	500 MHz	850 MHz	1950 MHz	2400 MHz	3500 MHz
Small Signal Gain	dB	15.4	15.2	15.0	13.6	13.3	12.5
Output Third Order Intercept Point	dBm		26.1	26.2	24.1	22.6	
Output Power at 1dB Compression	dBm		11.4	11.6	10.9	10.1	
Input Return Loss	dB	27.0	25.6	23.6	20.3	20.4	21.8
Output Return Loss	dB	20.8	22.9	28.0	21.5	19.4	22.7
Reverse Isolation	dB	18.2	18.4	18.6	19.1	19.1	18.9
Noise Figure	dB		3.7	3.6	3.8	4.3	

Test Conditions: $V_S = 5V$, $I_D = 35\,mA$ Typ., OIP_3 Tone Spacing $= 1\,MHz$, P_{OUT} per tone $= -5\,dBm$, $R_{BIAS} = 68\,\Omega$, $T_L = 25°C$, $Z_S = Z_L = 50\,\Omega$

OIP₃ vs. Frequency
V_D= 2.6 V, I_D= 35 mA (Typ.)

P₁dB vs. Frequency
V_D= 2.6 V, I_D= 35 mA (Typ.)

Noise Figure vs. Frequency
V_D= 2.6 V, I_D= 35 mA (Typ.)

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Typical RF Performance Over Temperature (Bias: V$_D$=2.6V, I$_D$=35mA)

$\left|S_{21}\right|$ vs. Frequency

$\left|S_{11}\right|$ vs. Frequency

$\left|S_{12}\right|$ vs. Frequency

$\left|S_{22}\right|$ vs. Frequency

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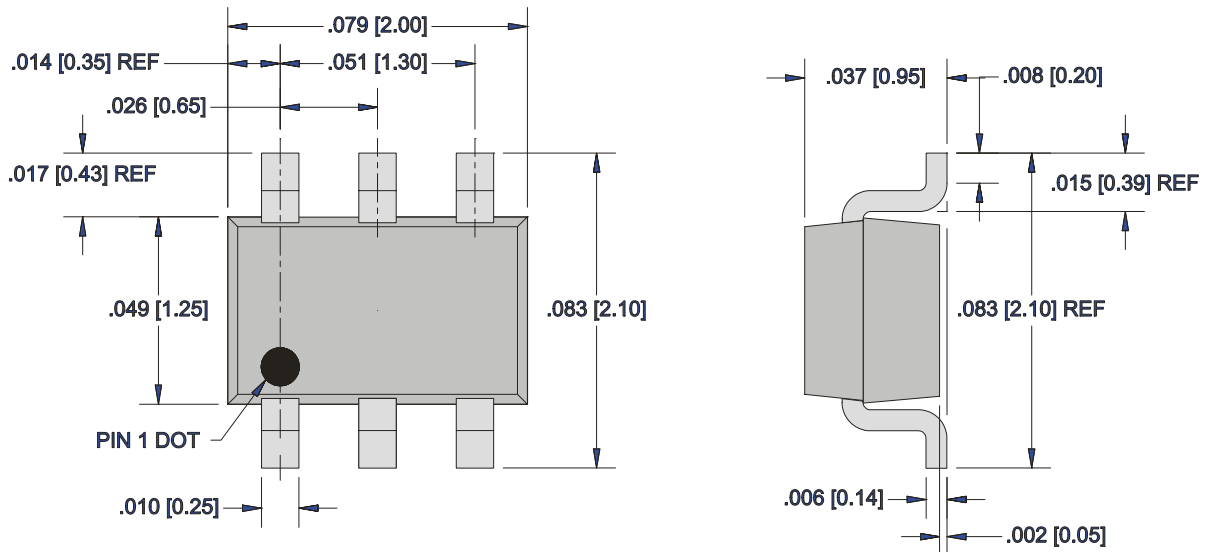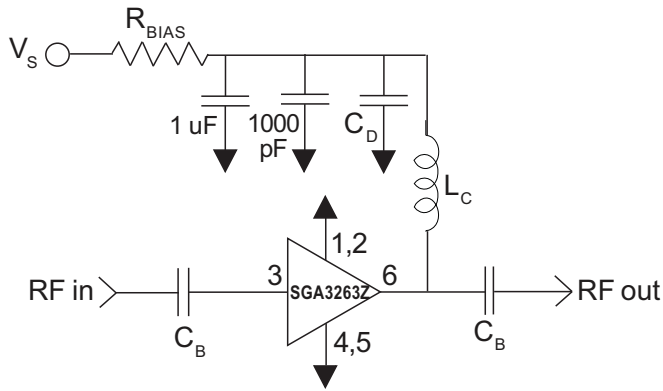| Pin	Function	Description
3	RF IN	RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.
1, 2, 4, 5	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
6	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefor a DC-blocking capacitor is necessary for proper operation.

Suggested Pad Layout

Dimensions in inches [millimeters]

Notes:
1. Provide a large ground pad area under device pins 1, 2, 4, & 5 with many plated via holes as shown.
2. Dimensions given for 50 Ohm RF I/O lines are for 31 mil thick Getek. Scale accordingly for different board thicknesses and dielectric contants.
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick Getek with 1 ounce copper on both sides.

Package Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.

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5 of 7

SGA3263Z

Application Schematic

Reference Designator	Frequency (Mhz)				
	500	850	1950	2400	3500
C_B	220 pF	100 pF	68 pF	56 pF	39 pF
C_D	100 pF	68 pF	22 pF	22 pF	15 pF
L_C	68 nH	33 nH	22 nH	18 nH	15 nH

| Recommended Bias Resistor Values for I_D=35mA R_{BIAS}=(V_S-V_D) / I_D				
Supply Voltage(V_S)	5 V	8 V	10 V	12 V
R_{BIAS}	68 Ω	150 Ω	200 Ω	270 Ω
Note: R_{BIAS} provides DC bias stability over temperature.				

Evaluation Board Layout
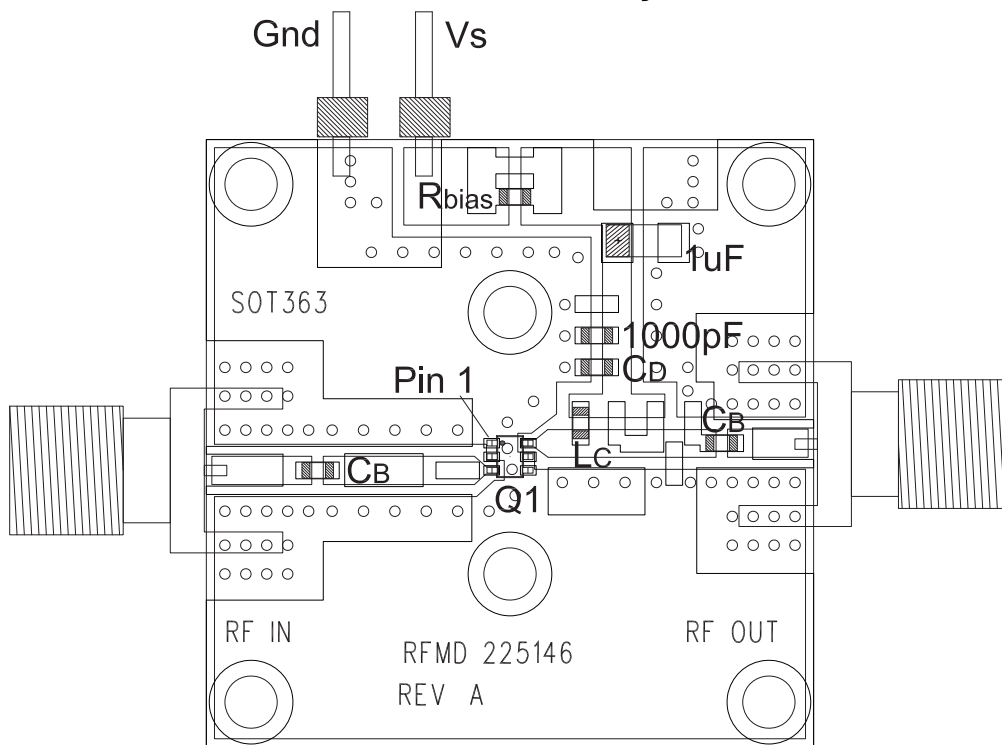
Mounting Instructions:

1. Use a large droung pad area near device pins 1, 2, 4, and 5 with plated through-holes as shown.

2. We recommend 1 or 2 ounces copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Part Identification
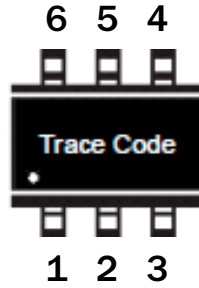
Ordering Information

Ordering Code	Description
SGA3263Z	7" Reel with 3000 pieces
SGA3263ZSQ	Sample bag with 25 pieces
SGA3263ZSR	7" Reel with 100 pieces
SGA3263ZPCK1	850MHz, 5V Operation PCBA with 5-piece sample bag

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7 of 7